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## INFORMATION DISCLOSURE

## STATEMENT BY APPLICANT

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|----------------------|-----------------|
| Application Number   | 09/943134       |
| Filing Date          | August 30, 2001 |
| First Named Inventor | Forbes, Leonard |
| Group Art Unit       | 2818            |
| Examiner Name        | Ho, Tu-Tu       |

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Attorney Docket No: 1303.020US1

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